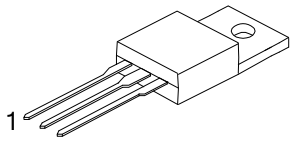
UF110N06

Preliminary | ***Power MOSFET***

110A, 60V N-CHANNEL POWER MOSFET



TO-220

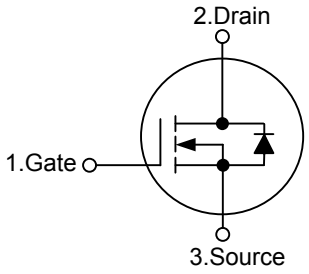
■ DESCRIPTION

The UTC **UF110N06** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

* Fast switching speed
* $R_{DS(ON)}$ < 12mΩ @ V_{GS} =10V, I_D =55A
* 100% avalanche tested
* Improved dv/dt capability

■ SYMBOL



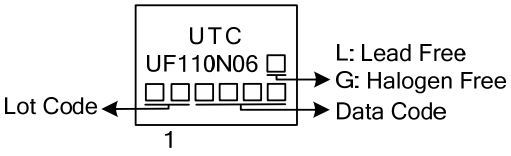
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF110N06L-TA3-T	UF110N06G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

UF110N06L-TA3-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube (2) TA3: TO-220 (3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	110	A
	Pulsed	I_{DM}	440	A
Avalanche Current (Note 2)		I_{AR}	110	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	605	mJ
Peak Diode Recovery dv/dt		dv/dt	4	V/ns
Power Dissipation		P_D	100	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 0.1mH, I_{AS} = 110A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 30A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

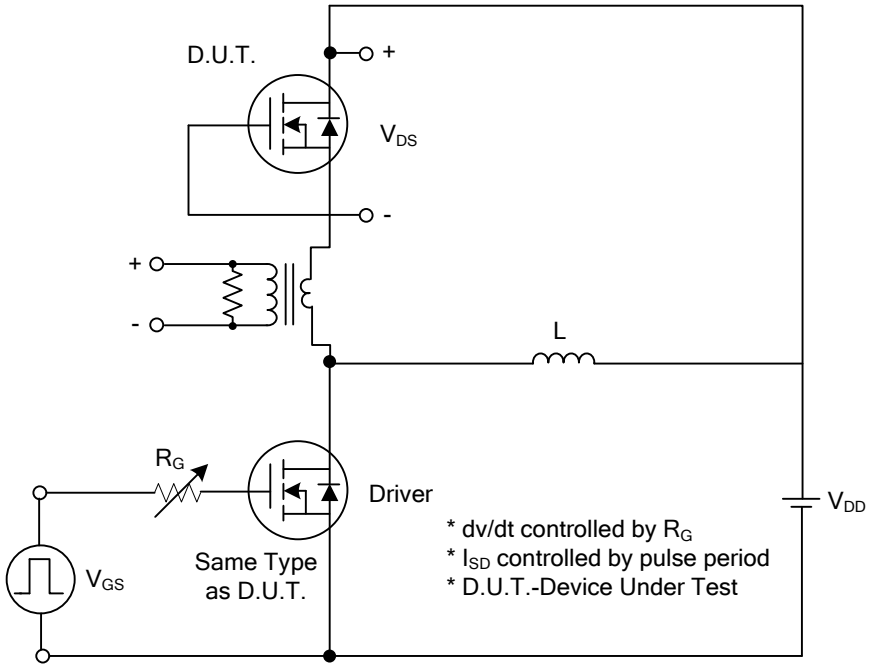
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	θ_{JC}	1.25	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise noted)

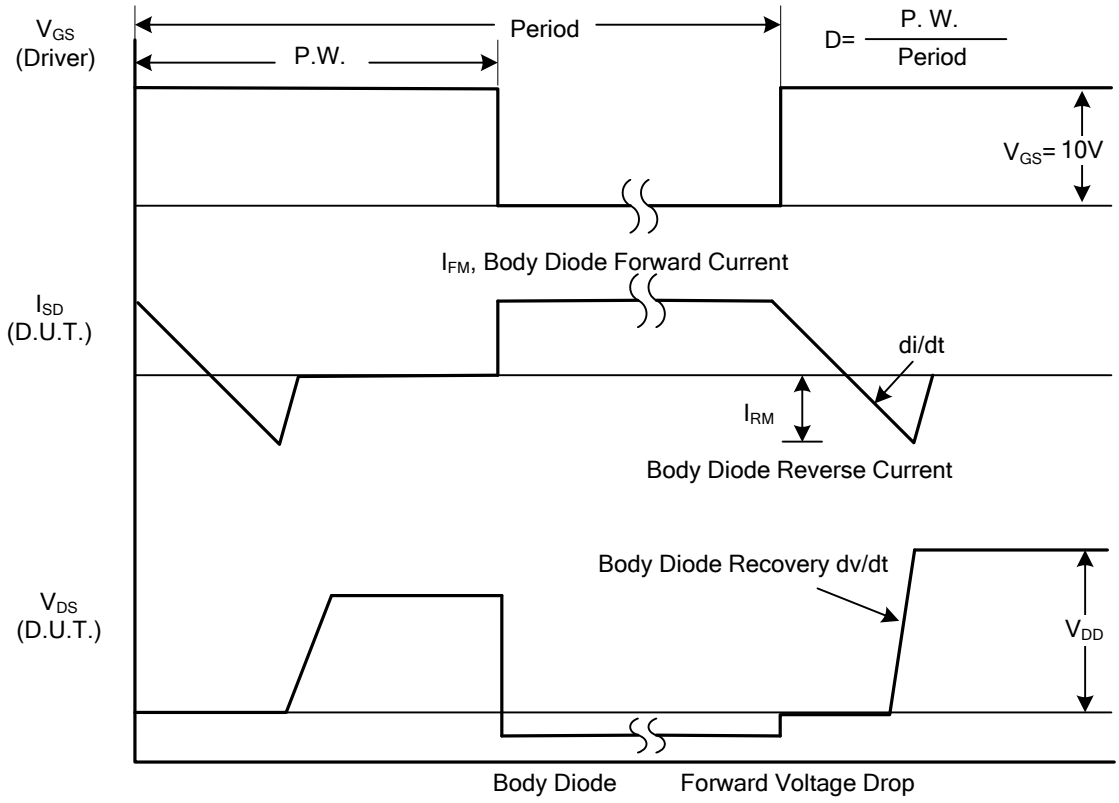
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} =0V, I_D =250 μA	60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=60V,V_{GS} =0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{DS}=0V, V_{GS}=+20V			+100	nA
	Reverse		V_{DS}=0V, V_{GS}=-20V			-100	nA
ON CHARACTERISTICS(Note1)							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=55A			12	mΩ
DYNAMIC PARAMETERS (Note 2)							
Input Capacitance		C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz		2810		pF
Output Capacitance		C_{OSS}			715		pF
Reverse Transfer Capacitance		C_{RSS}			105		pF
SWITCHING PARAMETERS(Note 2)							
Total Gate Charge		Q_G	V_{DS}=50V, V_{GS}=10V, I_D=1.3A, I_G=100μA (Note 1, 2)		290		nC
Gate Source Charge		Q_{GS}			20		nC
Gate Drain Charge		Q_{GD}			32		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=30V, V_{GS}=10V, I_D=0.5A, R_G = 25Ω (Note 1, 2)		88		ns
Turn-ON Rise Time		t_R			175		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			860		ns
Turn-OFF Fall-Time		t_F			390		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Current		I_S				110	A
Maximum Body-Diode Pulsed Current		I_{SM}				440	A
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS}=0V, I_S=110A			1.4	V
Body Diode Reverse Recovery Time		t_{RR}	V_{GS}=0V, I_S=30A dI$_F$/dt=100A/μs (Note 1)		80		ns
Body Diode Reverse Recovery Charge		Q_{RR}			200		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

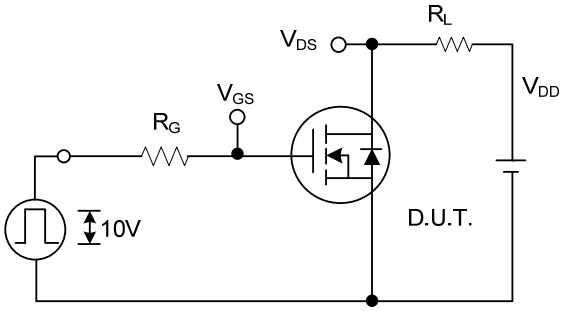


Peak Diode Recovery dv/dt Test Circuit

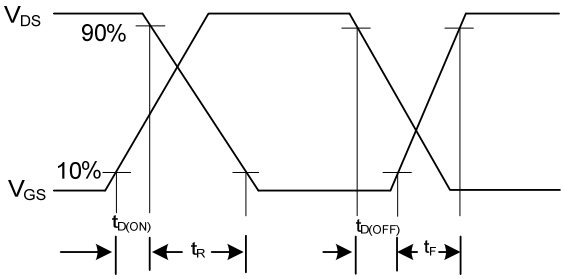


Peak Diode Recovery dv/dt Waveforms

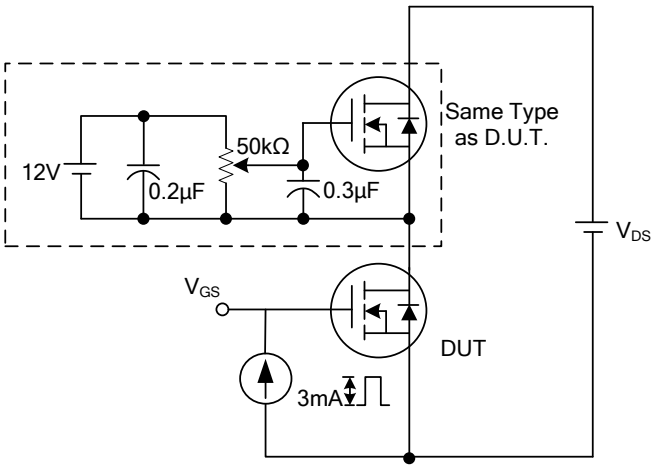
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



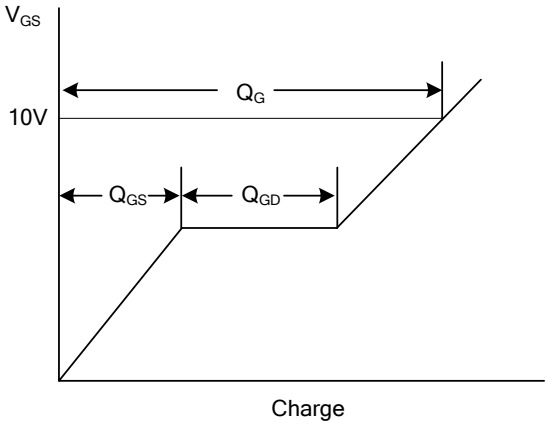
Switching Test Circuit



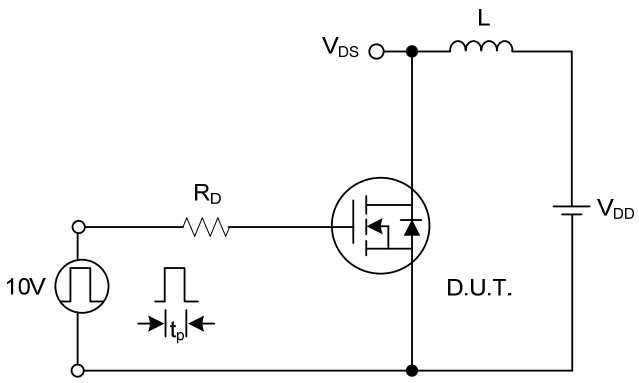
Switching Waveforms



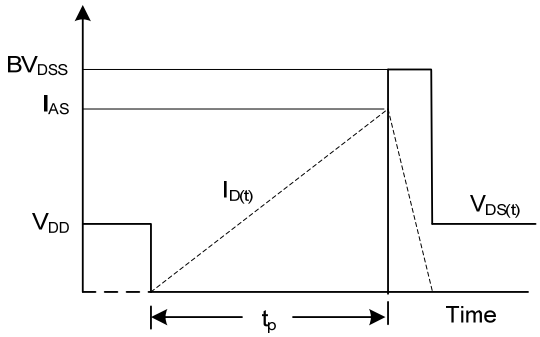
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms